

ABSTRACT OF THE DISCLOSURE

To provide a semiconductor device that can effectively suppress the short channel effect without deterioration of carrier migration, ^{an} ~~An~~ impurity ion is added from a direction of the <110> axis with respect to a silicon substrate on forming a punch through stopper under the gate electrode. In this invention, because the addition of the impurity is conducted by utilizing the principal of channeling, the impurity can be added ^a ~~with~~ small amount of scattering suppressing damages on the surface of the silicon substrate. A channel forming region having an extremely small impurity concentration and substantially no crystallinity disorder _{is formed}